

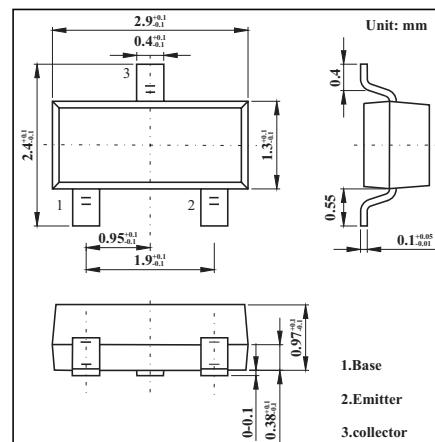
SOT-23 Plastic-Encapsulate Transistors

FEATURES

- High DC current gain
- High emitter-base voltage
- Low VCE (sat)

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage	V _{CBO}	25	V
Collector-emitter voltage	V _{CEO}	20	V
Emitter-base voltage	V _{EBO}	12	V
Collector current	I _C	0.5	A
		1	
Collector power dissipation	P _C	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 ~ +150	°C

* Single pulse Pw=100ms

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	B _{VCBO}	I _C =10uA	25			V
Collector-emitter breakdown voltage	B _{VCEO}	I _C =1mA	20			V
Emitter-base breakdown voltage	B _{VEBO}	I _E =10uA	12			V
Collector cutoff current	I _{CBO}	V _{CB} =20V			0.5	A
Emitter cutoff current	I _{EBO}	V _{EB} =10V			0.5	A
Collector-emitter saturation voltage	V _{CE(sat)}	I _C /I _B =500mA/20mA		0.18	0.4	V
DC current transfer ratio	h _{FE}	V _{CE} =3V, I _C =10mA	820		2700	
Output capacitance	f _T	V _{CE} =10V, I _E =-50mA, f=100MHz		350		MHz
Transition frequency	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz		8.0		pF
Output On-resistance	R _{on}	I _B =1mA, V _i =100mV(rms), f=1kHz		0.8		

*Measured using pulse current